

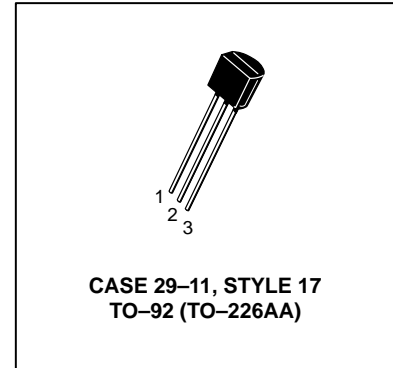
Darlington Transistors

NPN Silicon

BC517

MAXIMUM RATINGS

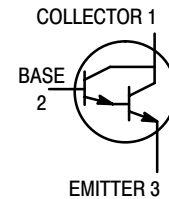
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	30	Vdc
Collector–Base Voltage	V_{CB}	40	Vdc
Emitter–Base Voltage	V_{EB}	10	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 12	mW mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



CASE 29–11, STYLE 17
TO–92 (TO–226AA)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 2.0 \text{ mAdc}, V_{BE} = 0$)	$V_{(BR)CES}$	30	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100 \text{ nAdc}, I_C = 0$)	$V_{(BR)EBO}$	10	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$)	I_{CES}	—	—	500	nAdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	—	100	nAdc

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS⁽¹⁾					
DC Current Gain ($I_C = 20 \text{ mAdc}$, $V_{CE} = 2.0 \text{ Vdc}$)	h_{FE}	30,000	—	—	—
Collector–Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}$, $I_B = 0.1 \text{ mAdc}$)	$V_{CE(\text{sat})}$	—	—	1.0	Vdc
Base–Emitter On Voltage ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	$V_{BE(\text{on})}$	—	—	1.4	Vdc
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product ⁽²⁾ ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	—	200	—	MHz

1. Pulse Test: Pulse Width $\leq 2.0\%$.

2. $f_T = |h_{fe}| \cdot f_{\text{test}}$

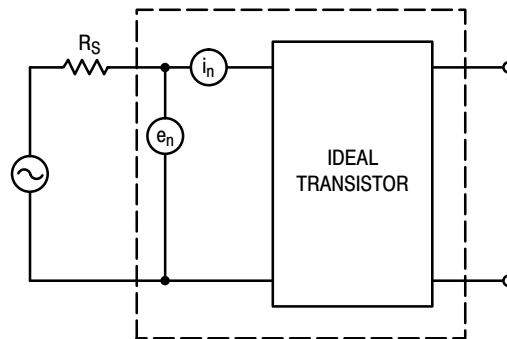


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

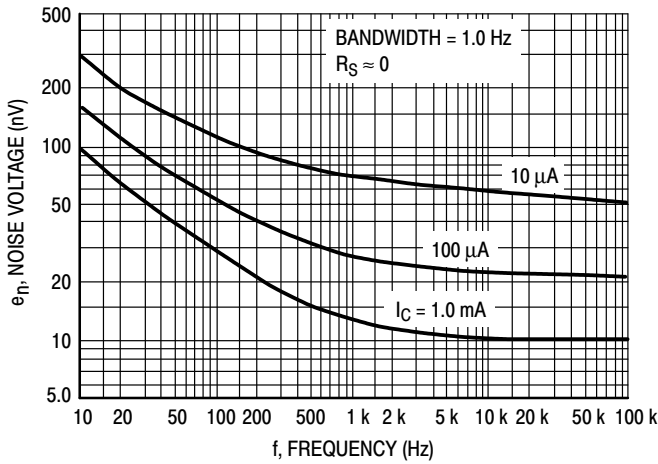


Figure 2. Noise Voltage

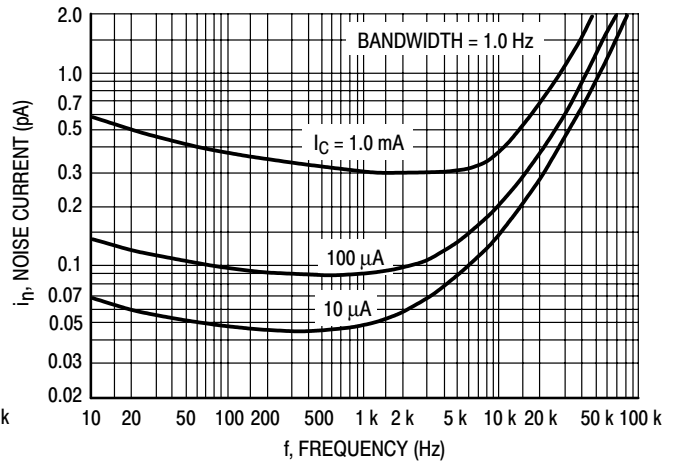


Figure 3. Noise Current

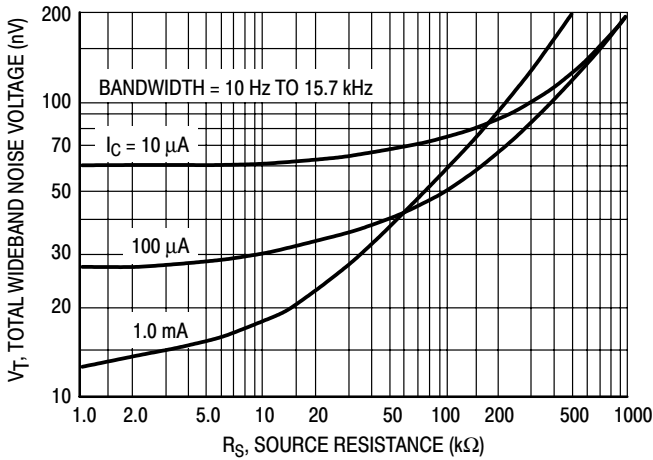


Figure 4. Total Wideband Noise Voltage

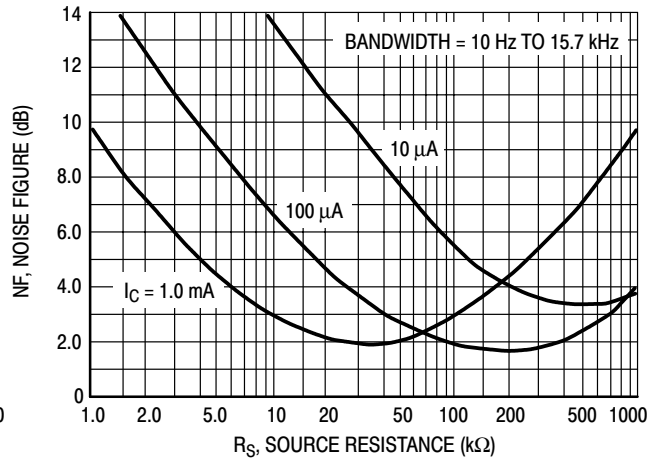


Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

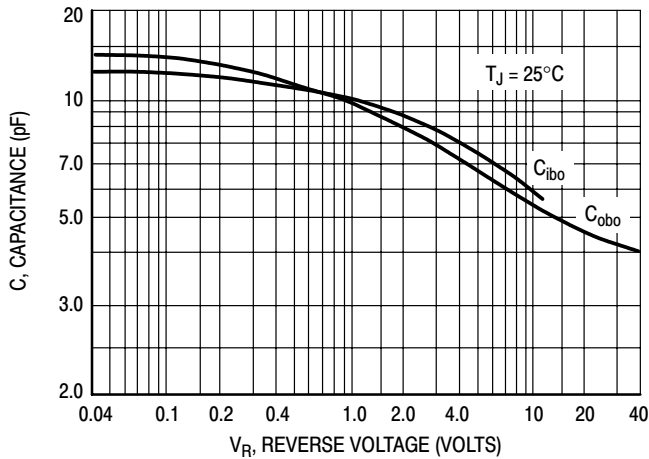


Figure 6. Capacitance

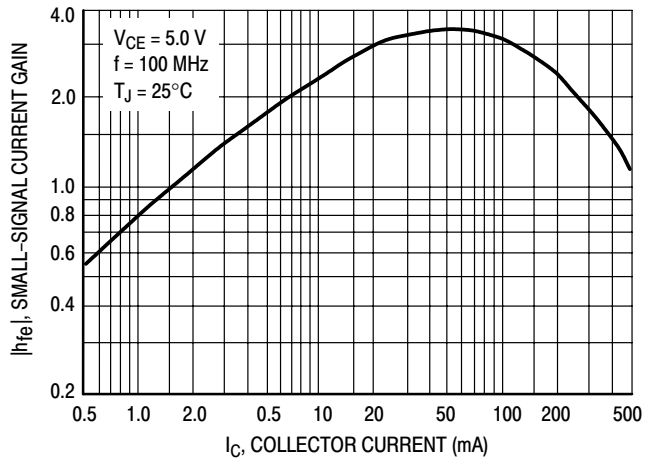


Figure 7. High Frequency Current Gain

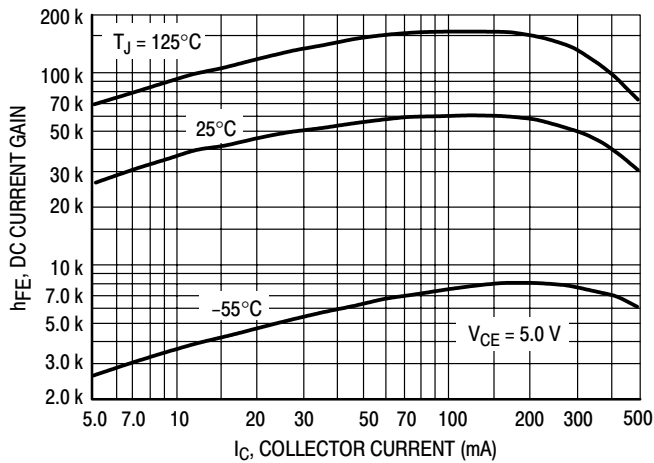


Figure 8. DC Current Gain

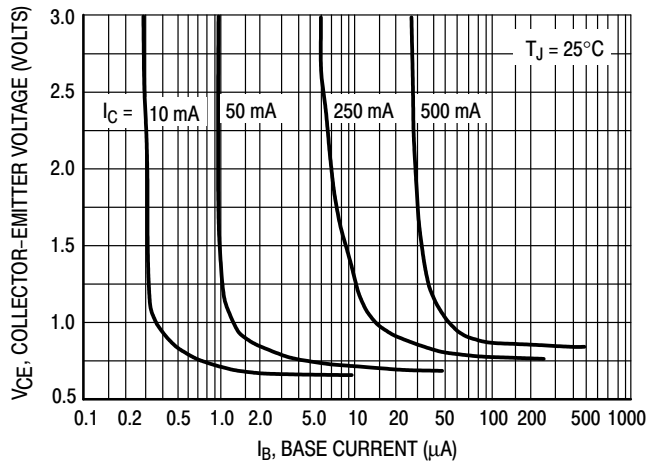


Figure 9. Collector Saturation Region

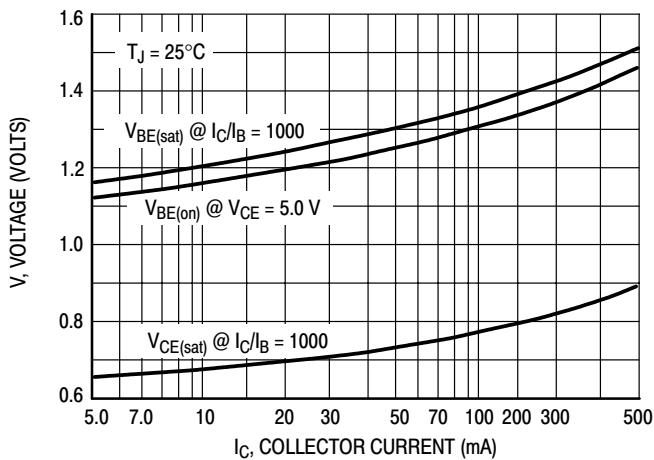


Figure 10. "On" Voltages

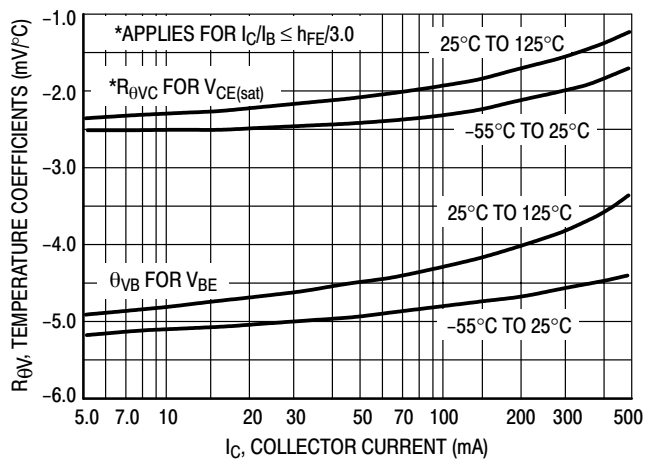


Figure 11. Temperature Coefficients

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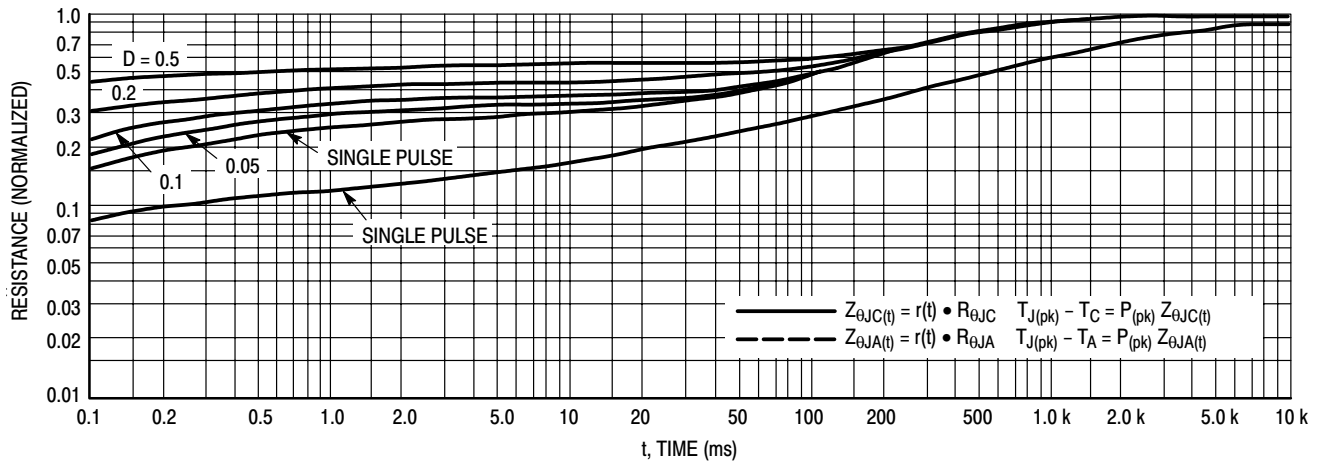


Figure 12. Thermal Response

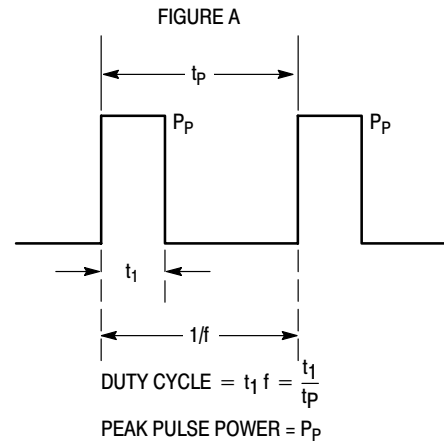
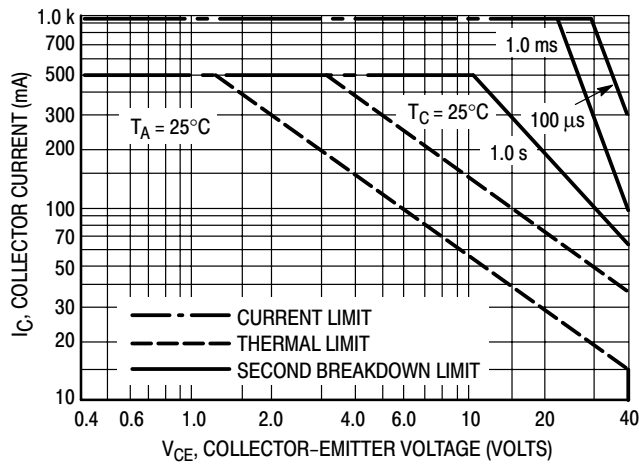


Figure 13. Active Region Safe Operating Area Design Note: Use of Transient Thermal Resistance Data